

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

3A  
2/4/02

Applicant: Yushi HORIUCHI et al.

Title: SILICON/SILICON CARBIDE COMPOSITE AND PROCESS FOR  
MANUFACTURING THE SAME

Appl. No.: Unassigned

Filing Date: DEC 21 2000

Examiner: Unassigned

Art Unit: Unassigned

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
Box PATENT APPLICATION  
Washington, D.C. 20231

Sir:

Prior to examination, Applicants respectfully request that the above-identified application be amended as follows:

**IN THE CLAIMS:**

In accordance with 37 C.F.R. § 1.21, please substitute for claims 3, 4, 8, 9, 11, 12 and 15 the following rewritten version of the same claims, as. The changes are shown explicitly in the attached "Version with Markings to Show Changes Made."

Sub B2  
A1  
3. (Amended) A silicon/silicon carbide composite according to claim 1, wherein said silicon/silicon carbide composite includes a dummy wafer with a silicon carbide film having a thickness of 30 to 150  $\mu$ m formed on the surface thereof, said dummy wafer having a total thickness of 0.5 to 1 mm.